ABSTRACT OF THE DISCLOSURE

TITLE OF INVENTION: **SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND METHOD FOR MANUFACTURING THE SAME**

In a semiconductor integrated circuit device having a high breakdown voltage CMOS transistor integrated for programming a programmable element, the present invention is intended to solve a problem that the drain breakdown voltage of the high breakdown voltage transistor goes low as a result of a structure that the standard transistor and the high breakdown voltage transistor share a channel dope region in common. On a P-type monocrystal silicon substrate of 10 - 20 Ωcm specific resistivity having P-well region and silicon oxide film for separating the elements, a channel dope region for insulated-gate type field effect transistor A and that for inulated-gate type field effect transistor B are formed separately, making the impurity concentration in a channel dope region twice to ten times as high that in the other channel dope region. By so doing, the characteristics of the two kinds of insulated-gate type field effect transistors may be controlled independently, dispersion in the electrical characteristics of the high breakdown voltage CMOS transistor suppressed, and the area for the same made smaller.

Figure 1.